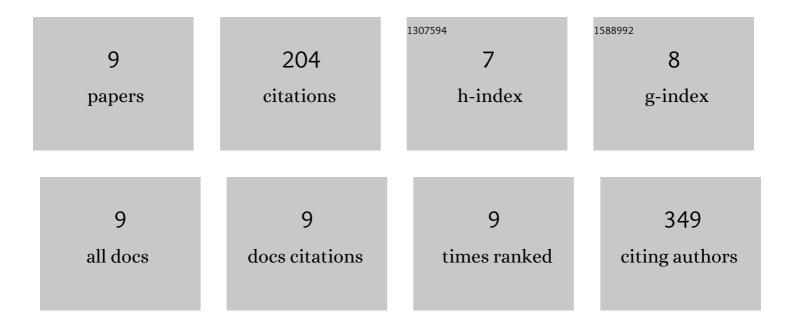
## Seung-Geun Kim

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/12143862/publications.pdf Version: 2024-02-01



#	Article	IF	CITATIONS
1	Infrared Detectable MoS <sub>2</sub> Phototransistor and Its Application to Artificial Multilevel Optic-Neural Synapse. ACS Nano, 2019, 13, 10294-10300.	14.6	96
2	Hysteresis Modulation on Van der Waalsâ€Based Ferroelectric Fieldâ€Effect Transistor by Interfacial Passivation Technique and Its Application in Optic Neural Networks. Small, 2020, 16, e2004371.	10.0	35
3	Schottky Barrier Height Modulation Using Interface Characteristics of MoS <sub>2</sub> Interlayer for Contact Structure. ACS Applied Materials & amp; Interfaces, 2019, 11, 6230-6237.	8.0	19
4	Reduction of Threshold Voltage Hysteresis of MoS <sub>2</sub> Transistors with 3-Aminopropyltriethoxysilane Passivation and Its Application for Improved Synaptic Behavior. ACS Applied Materials & Interfaces, 2019, 11, 20949-20955.	8.0	19
5	Enhancement of Synaptic Characteristics Achieved by the Optimization of Proton–Electron Coupling Effect in a Solid‣tate Electrolyteâ€Gated Transistor. Small, 2021, 17, e2100242.	10.0	13
6	Super steep-switching (SS â‰^ 2 mV/decade) phase-FinFET with Pb(Zr0.52Ti0.48)O3 threshold switching device. Applied Physics Letters, 2018, 113, .	3.3	8
7	Analysis of the Thermal Degradation Effect on a HfO <sub>2</sub> -Based Memristor Synapse Caused by Oxygen Affinity of a Top Electrode Metal and on a Neuromorphic System. ACS Applied Electronic Materials, 2021, 3, 5584-5591.	4.3	8
8	Ultralow Schottky Barrier Height Achieved by Using Molybdenum Disulfide/Dielectric Stack for Source/Drain Contact. ACS Applied Materials & Interfaces, 2019, 11, 34084-34090.	8.0	6
9	An Electrical Analysis of a Metal-Interlayer-Semiconductor Structure on High-Quality Si1â^'x Gex Films for Non-Alloyed Ohmic Contact. Journal of Nanoscience and Nanotechnology, 2017, 17, 7323-7326.	0.9	0